# JIEJIE MICROELECTRONICS CO., Ltd

### KxxxxG Series Sidac

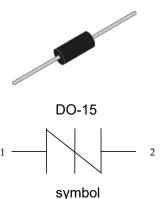
Rev.3.1

#### **DESCRIPTION:**

The sidac is a silicon bilateral voltage triggered switch with greater power-handling capabilities than standard diacs. Upon application of a voltage exceeding the sidac breakover voltage point, the sidac switches on through a negative resistance region to a low on-state voltage. Conduction continues until the current is interrupted or drops below the minimum holding current of the device.

#### **APPLICATIONS:**

- ♦ High-voltage lamp ignitors
- ♦ Natural gas ignitors
- ♦ Gas oil ignitors
- ♦ High-voltage power supplies
- ♦ Xenon ignitors
- ♦ Overvoltage protector
- ♦ Pulse generators
- ♦ Fluorescent lighting ignitors HID lighting ignitors



#### **FEATURES:**

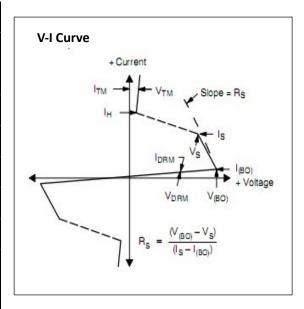
- Excellent capability of absorbing transient surge
- ♦ Quick response to surge voltage (ns Level)
- ♦ Glass-passivated junctions
- ♦ High voltage lcmp ignitors

### **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Storage temperature range	Tstg	-40 to +125	$^{\circ}$ C
Operating junction temperature range	TJ	-40 to +125	$^{\circ}$ C
On-state RMS current	Ιτ	1.0	Α
Maximum surge on-state current non-repetitive one cycle peak value (50Hz)	Ітѕм	16.7	Α
Critical rate-of-rise of on-state current	di⊤/dt	80	A/µs

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C)

Symbol	Parameter		
V <sub>DRM</sub>	Peak off-state voltage		
IDRM	Off-state current		
Vs	Switching voltage		
Is	Switching current		
Rs	Switching resistance		
VT	On-state voltage		
Ін	Holding current		
V <sub>BO</sub>	Breakover Voltage		
Іво	Breakover current		

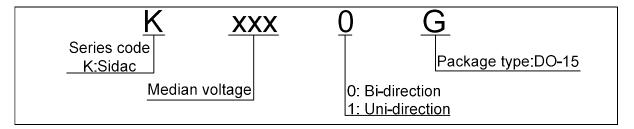


### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub>=25°C, continued)

	IDRM@	)V <sub>DRM</sub>	Vı	ВО	Іво	V <sub>T</sub> @ I <sub>T</sub> =1A	Ін	Rs	
Part Number	μA	V	\	/	μA	V	mA	kΩ	Marking
	max	min	min	max	max	max	min	min	
K0900G	1	70	80	97	50	2	10	0.1	DB090
K1050G	1	90	95	113	50	2	10	0.1	DB105
K1200G	1	100	110	125	50	2	10	0.1	DB120
K1300G	1	110	120	138	50	2	10	0.1	DB130
K1400G	1	120	130	146	50	2	10	0.1	DB140
K1500G	1	130	140	170	50	2	10	0.1	DB150
K1800G	1	160	170	195	50	2	10	0.1	DB180
K2000G	1	180	190	215	50	2	10	0.1	DB200BW
K2200G	1	190	205	230	50	2	10	0.1	DB220BW
K2400G	1	200	220	250	50	2	10	0.1	DB240BW
K2600G	1	220	240	270	50	2	10	0.1	DB260BW



## **ORDERING INFORMATION**



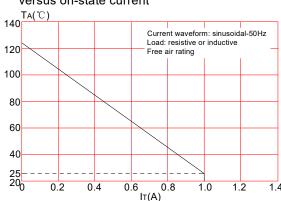
### **MARKING**



### **SOLDERING PARAMETERS**

Reflow Conditi	on	Pb-Free assembly (see FIG.2)	
	-Temperature Min (T <sub>s(min)</sub> )	+150℃	
Pre Heat	-Temperature Max(T <sub>s(max)</sub> )	+200℃	
	-Time (Min to Max) (ts)	60-180 secs.	
Average ramp	up rate (Liquidus Temp (T <sub>L</sub> ) to peak)	3℃/sec. Max	
T <sub>s(max)</sub> to T <sub>L</sub> - R	Γ <sub>s(max)</sub> to T <sub>L</sub> - Ramp-up Rate 3°C/sec. Ma		
Reflow	-Temperature(T <sub>L</sub> ) (Liquidus)	+217℃	
	-Temperature(t <sub>L</sub> )	60-150 secs.	
Peak Temp (Tp	b)	+260(+0/-5)°C	
Time within 5°	ℂ of actual Peak Temp (tթ)	30 secs. Max	
Ramp-down Rate		6℃/sec. Max	
Time 25℃ to Peak Temp (T <sub>P</sub> )		8 min. Max	
Do not exceed		+260℃	

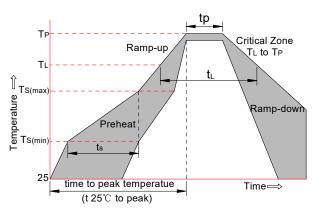
**FIG.1:** Maximum allowable ambient temperature versus on-state current



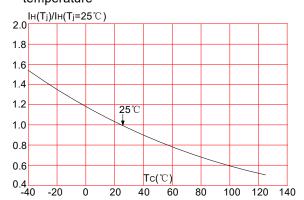
**FIG.3:** Normalized Vs change vs. junction temperature



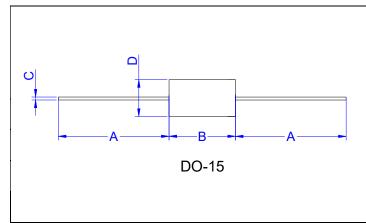
FIG.2: Reflow condition



**FIG.4:** Normalized DC holding current vs. case temperature

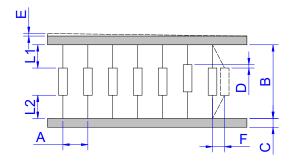


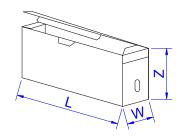
### **PACKAGE MECHANICAL DATA**



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	25.40	-	1.000	-	
В	5.80	7.62	0.228	0.300	
С	0.71	0.86	0.028	0.034	
D	2.60	3.60	0.102	0.142	

### **TAPE AND BOX SPECIFICATION-DO-15**





Ref.	Dimer	nsions		
Rei.	Millimeters	Inches		
Α	5.0±0.5	0.197±0.020		
В	53.0±1.5	2.087±0.059		
С	6.0±0.5	0.236±0.020		
D	1.2(MAX)	0.047(MAX)		
Е	0.8(MAX)	0.031(MAX)		
F	1.5(MAX)	0.059(MAX)		
L1-L2	1.0(MAX)	0.039(MAX)		
W	80±5.0	3.150±0.197		
L	250±5.0	9.843±0.197		
Z	115±5.0	4.528±0.197		

PART No.	UNIT WEIGHT (g/PCS) typ.	PER BOX (PCS)	PER CARTON (PCS)	DESCRIPTION
KxxxxG	0.42	2,000	20,000	Вох

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